ABSTRACT

METHOD FOR FORMING SILICON DIOXIDE FILM

[Problem] To provide a method capable of forming an insulating film suffering less from both shrinkage and stress.
[Means for solving] A method for forming a silicon dioxide film, comprising the steps of: coating a substrate with a polysilazane composition to form a coat, and then heating the formed coat in a hydrogen peroxide atmosphere at 50 to 200°C. This method enables to form isolation structures such as various insulating films.

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